L Number	Hits	Search Text	DB	Time stamp
1	2908855	memory or storage	USPAT;	2004/09/30 11:22
			US-PGPUB;	
			EPO; JPO;	
			DERWENT	
2	19603	(memory or storage) and (ferroelectric or ferro-electric)	USPAT;	2004/09/30 11:23
			US-PGPUB;	
			EPO; JPO;	
			DERWENT	
3	343	((memory or storage) and (ferroelectric or ferro-electric))	USPAT;	2004/09/30 11:24
		and transistor with capacitor with parallel	US-PGPUB;	
			EPO; JPO;	
			DERWENT	
4	59	(((memory or storage) and (ferroelectric or ferro-electric))	USPAT;	2004/09/30 11:25
		and transistor with capacitor with parallel) and column adj2	US-PGPUB;	
		decoder	EPO; JPO;	
			DERWENT	

L Number	Hits	Search Text	DB	Time stamp
1	2908855	memory or storage	USPAT;	2004/09/30 10:06
			US-PGPUB;	
			EPO; JPO;	
			DERWENT	
2	19603	(memory or storage) and (ferroelectric or ferro-electric)	USPAT;	2004/09/30 10:07
			US-PGPUB;	
			EPO; JPO;	
_			DERWENT	
3	343	((memory or storage) and (ferroelectric or ferro-electric))	USPAT;	2004/09/30 10:08
		and capacitor with transistor with parallel	US-PGPUB;	
			EPO; JPO;	
_	166		DERWENT	
5	166	(((memory or storage) and (ferroelectric or ferro-electric))	USPAT;	2004/09/30 10:31
:		and capacitor with transistor with parallel ) and plate adj line	US-PGPUB;	
			EPO; JPO;	
	4.5	////	DERWENT	2004/00/20 40 20
7	15	((((memory or storage) and (ferroelectric or ferro-electric))	USPAT;	2004/09/30 10:32
		and capacitor with transistor with parallel ) and plate adj	US-PGPUB;	
		line) and plate adj line adj driver and column adj3 decoder	EPO; JPO;	
			DERWENT	L